

1200V 40mohm Silicon Carbide Power MOSFET

AK1CK2M040WDM

Features:

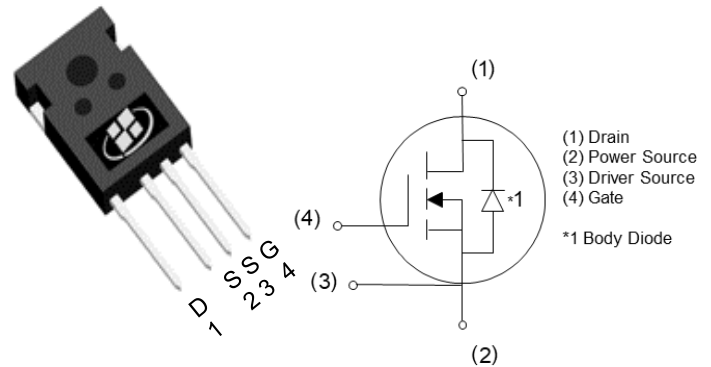
- Low on-resistance
- Fast switching speed with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{RR})
- Halogen-free, RoHS compliant ^(Note 1)

Applications:

- Motor drives
- DC/DC converters
- Switched mode power supplies
- Solar inverters

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	1200	V
$R_{DSON, TYP} @ V_{GS} = 15 V$	40	m Ω
$R_{DSON, TYP} @ V_{GS} = 18 V$	35	m Ω
I_D	62	A
P_D	333	W



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AK1CK2M040WDM	TO-247LP-4L	1CK2M040WDM	Tube	300 per box

Notes:

1. Contact ALKAIDSEMI sales for detail information

Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	1200	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) <small>(Note 1)</small>	62	A
	Drain Current - Continuous ($T_C = 100^\circ\text{C}$) <small>(Note 1)</small>	44	A
I_{DM}	Drain Current - Pulsed <small>(Note 2)</small>	155	A
V_{GS}	Gate-Source Voltage (dynamic)	-10/+22	V
V_{GS}	Gate-Source Voltage (static)	-6/+18	V
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	333	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Steady-State	0.45	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Steady-State	40	$^\circ\text{C}/\text{W}$

Notes:

1. The max drain current limited by maximum junction temperature
2. Pulse width is limited by safe operating area

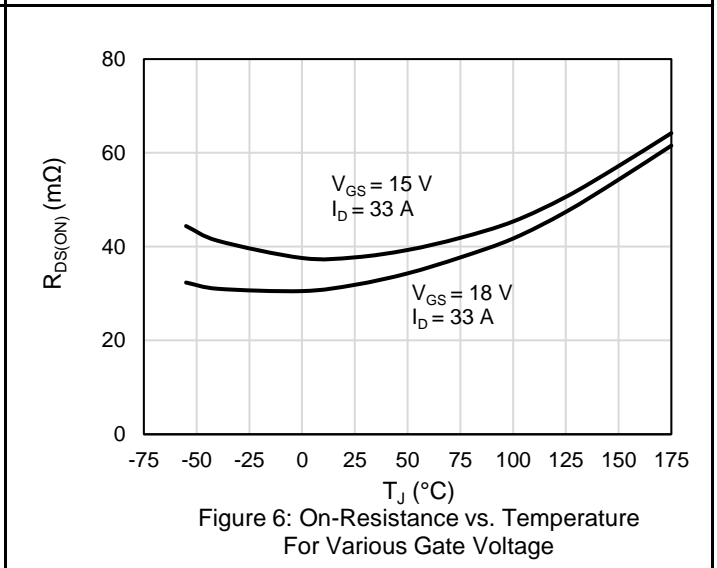
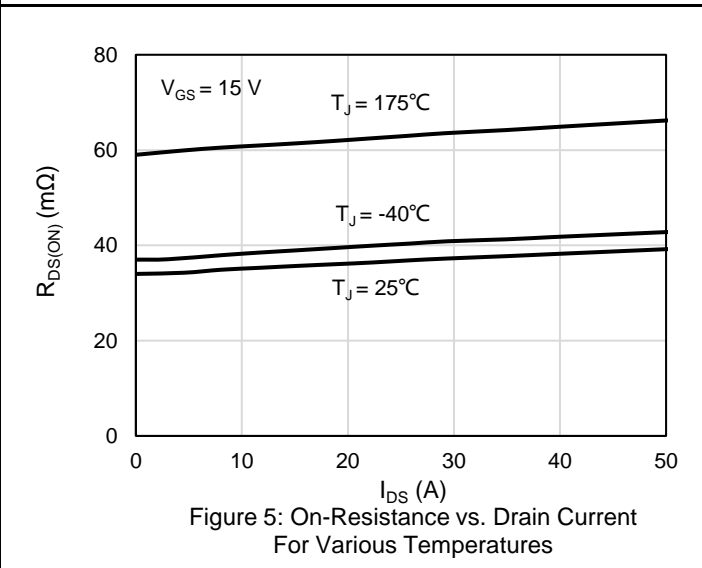
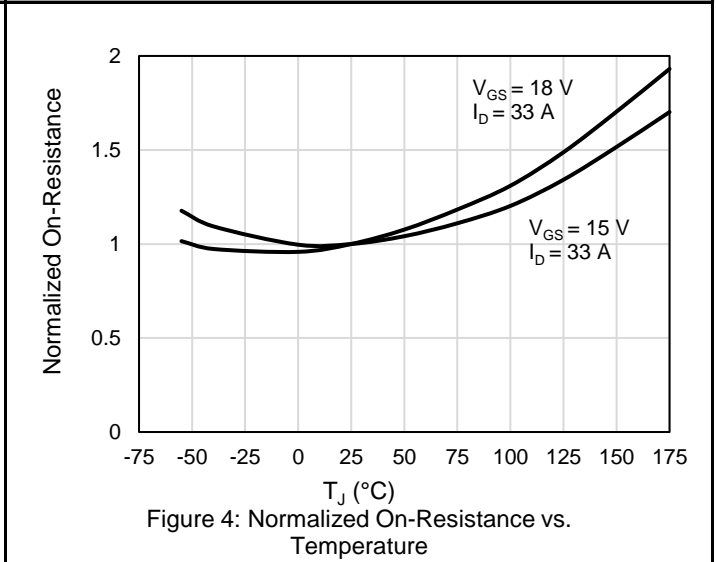
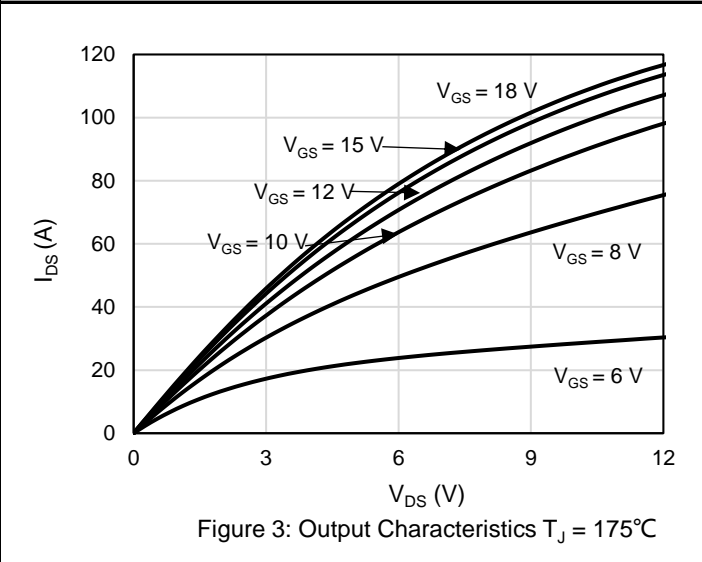
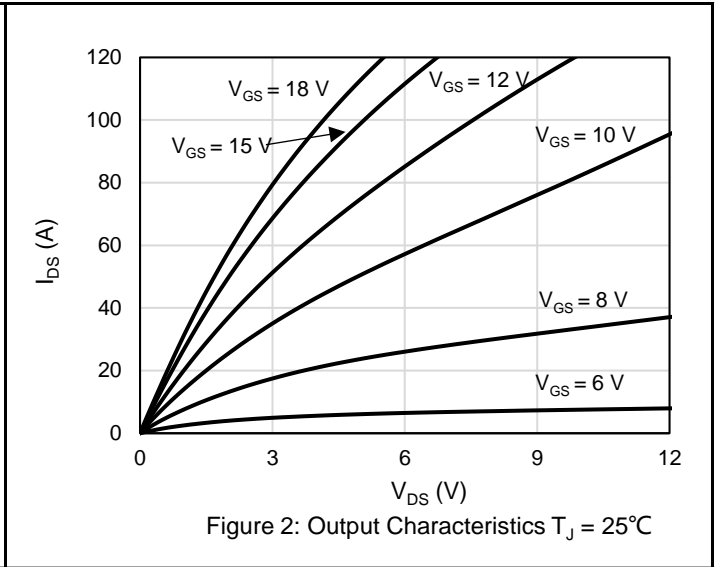
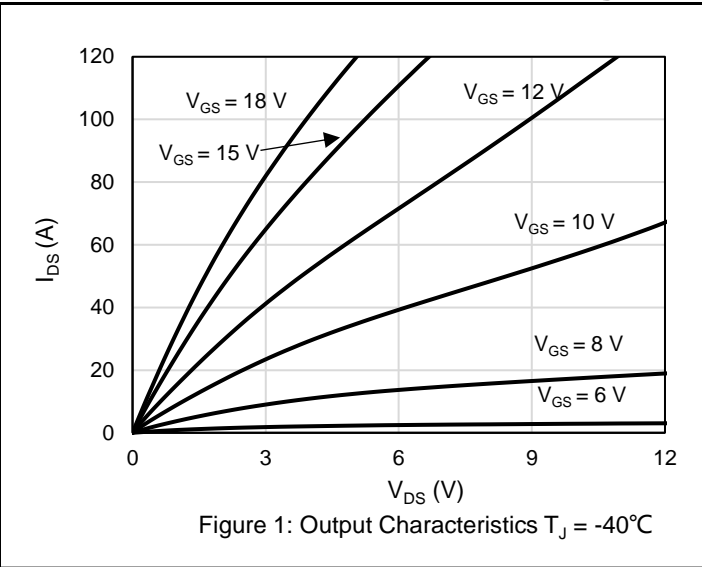
Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	1200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$		5	50	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = +22\text{ V}, V_{DS} = 0\text{ V}$			100	nA
		$V_{GS} = -10\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
$V_{GS(th)}$	Gate Threshold voltage	$V_{DS} = V_{GS}, I_D = 11\text{ mA}$	1.8	2.7	4	V
		$V_{DS} = V_{GS}, I_D = 11\text{ mA}, T_J = 175^\circ\text{C}$		1.8		V
$R_{DS(ON)}$	Drain-Source on-state resistance	$V_{GS} = 15\text{ V}, I_D = 33\text{ A}$		40	50	m Ω
		$V_{GS} = 15\text{ V}, I_D = 33\text{ A}, T_J = 175^\circ\text{C}$		66		m Ω
$R_{DS(ON)}$	Drain-Source on-state resistance	$V_{GS} = 18\text{ V}, I_D = 33\text{ A}$		35	45	m Ω
		$V_{GS} = 18\text{ V}, I_D = 33\text{ A}, T_J = 175^\circ\text{C}$		64		m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 20\text{ A}$		18		S
		$V_{DS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 175^\circ\text{C}$		20		S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}, F = 100\text{ kHz}, V_{AC} = 25\text{ mV}$		2600		pF
C_{OSS}	Output Capacitance			90		pF
C_{RSS}	Reverse Transfer Capacitance			6.5		pF
E_{OSS}	C_{OSS} Stored Energy			41		μJ
R_G	Gate Resistance	$F = 1\text{ MHz}, V_{AC} = 25\text{ mV}$		1.4		Ω
Q_{GS}	Gate-Source Charge	$V_{DS} = 800\text{ V}, I_D = 33\text{ A}, V_{GS} = -4/+15\text{ V}$		27		nC
Q_{GD}	Gate-Drain Charge			46		nC
Q_G	Total Gate Charge			113		nC

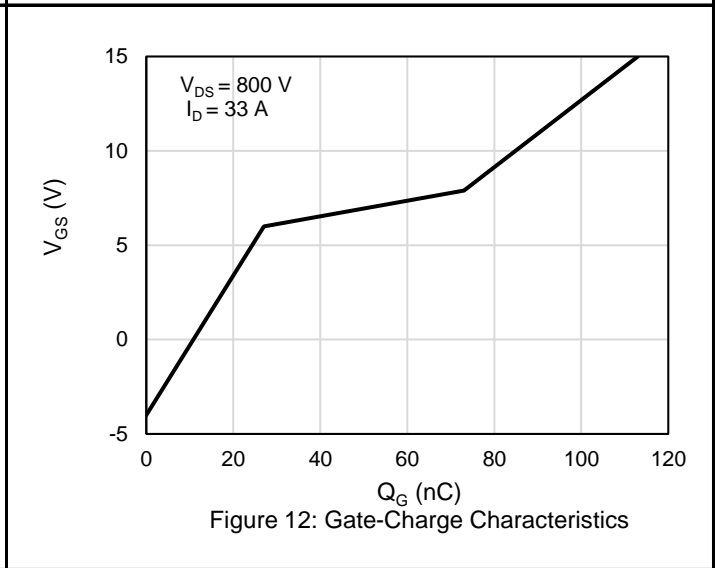
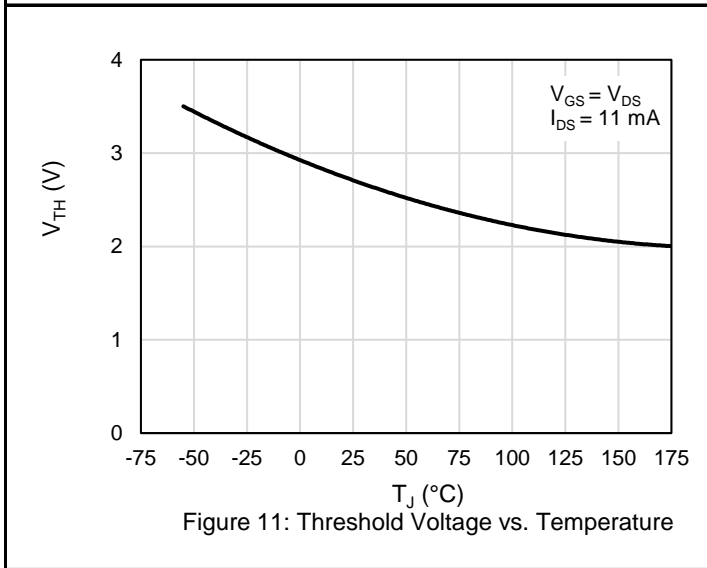
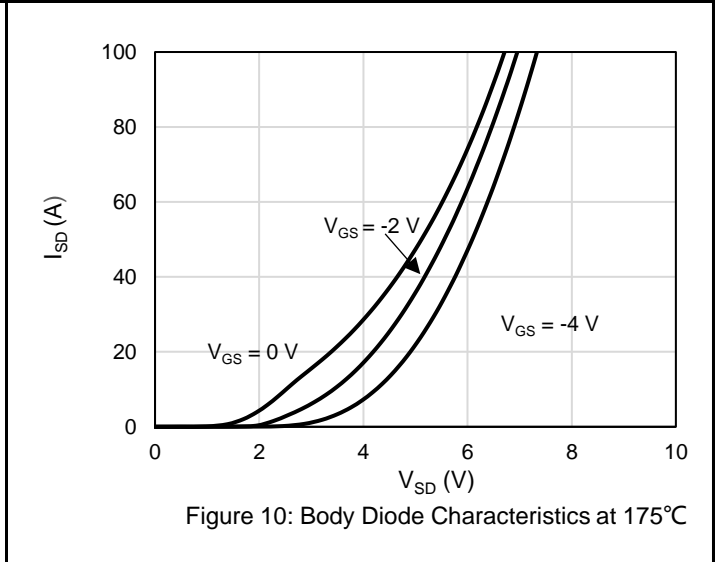
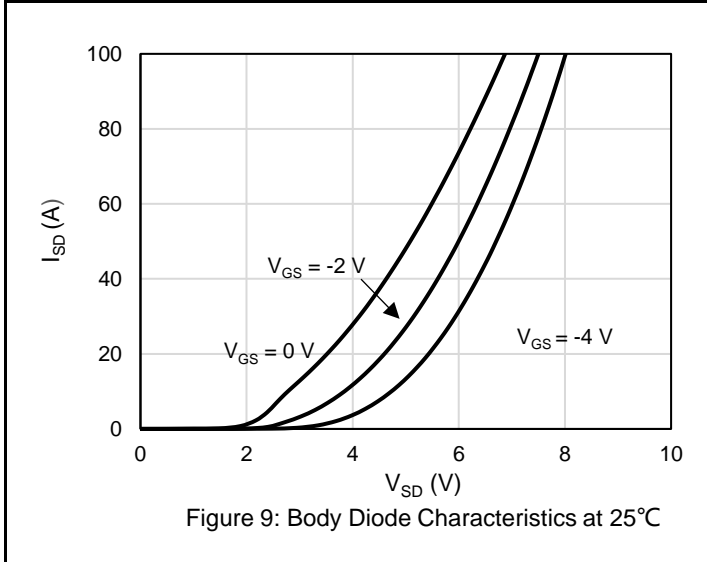
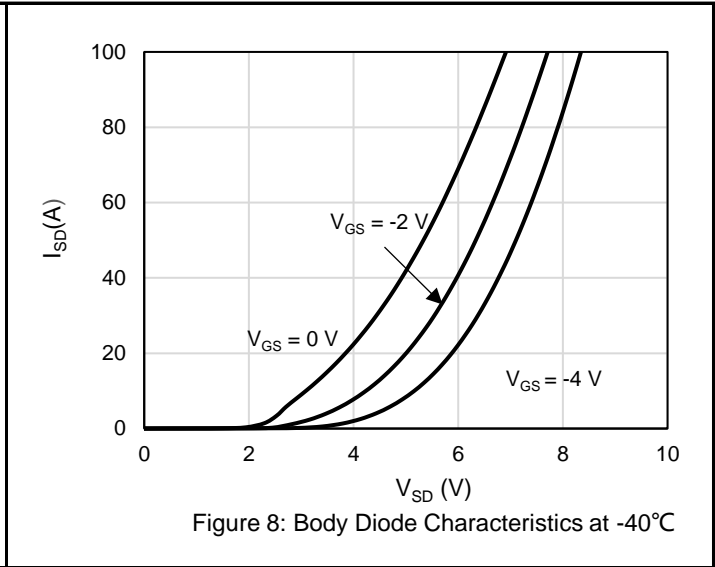
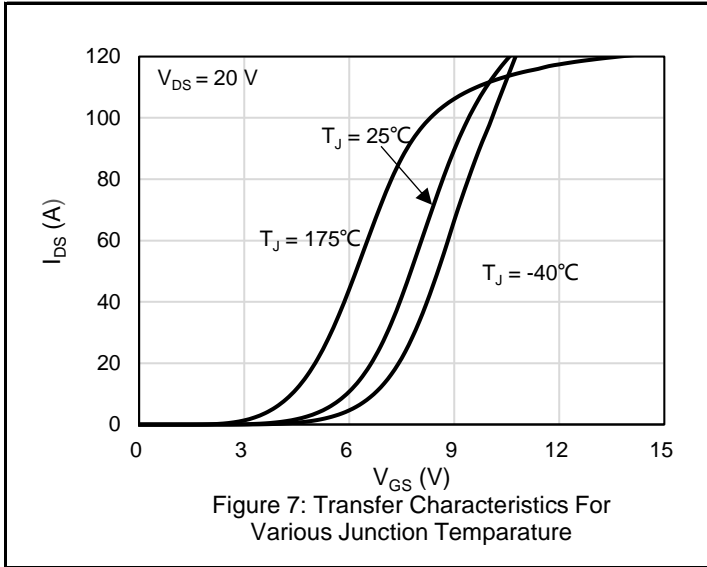
Switching Characteristics

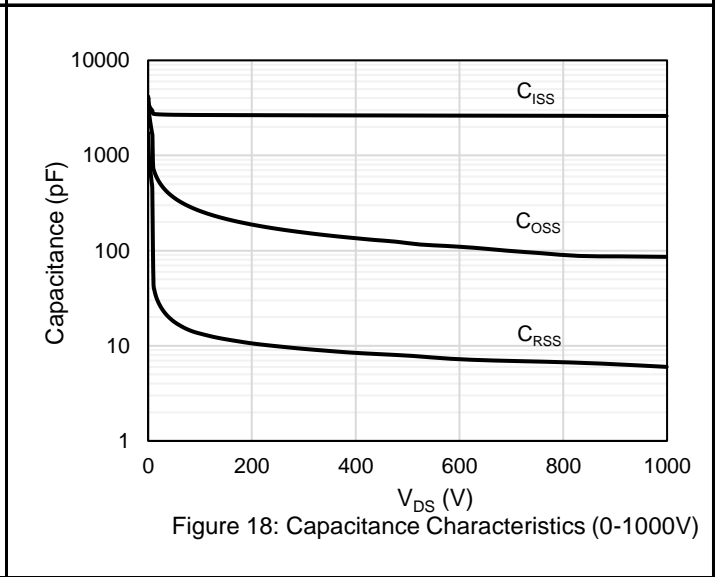
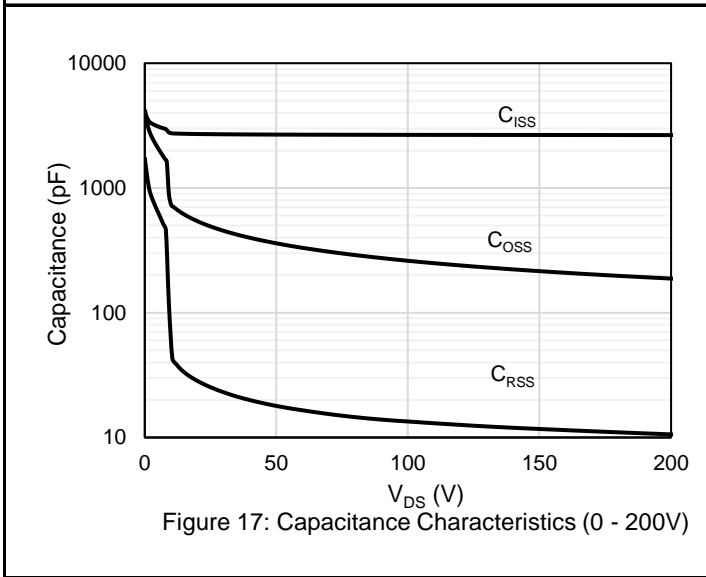
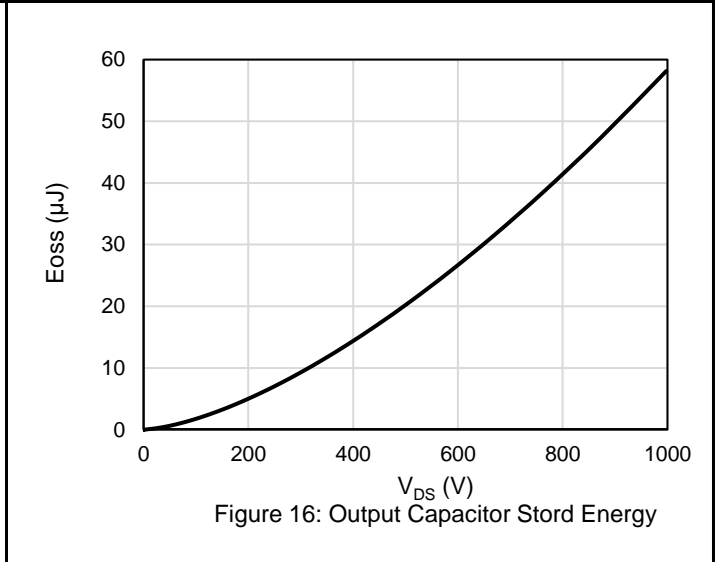
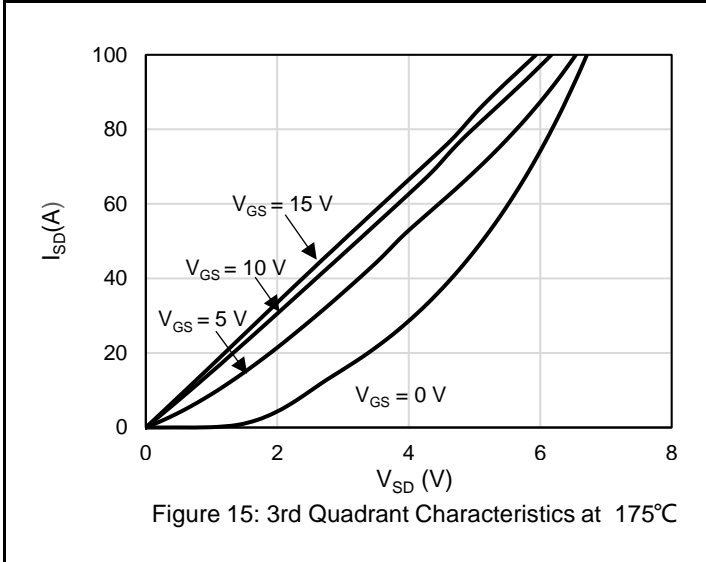
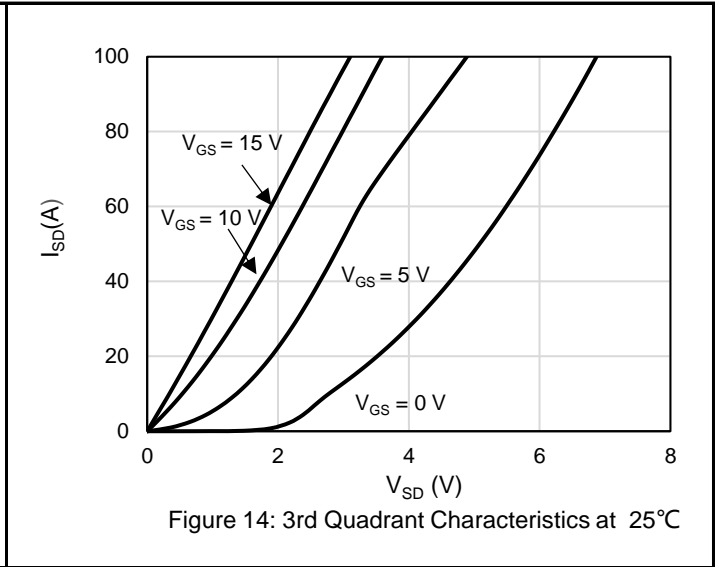
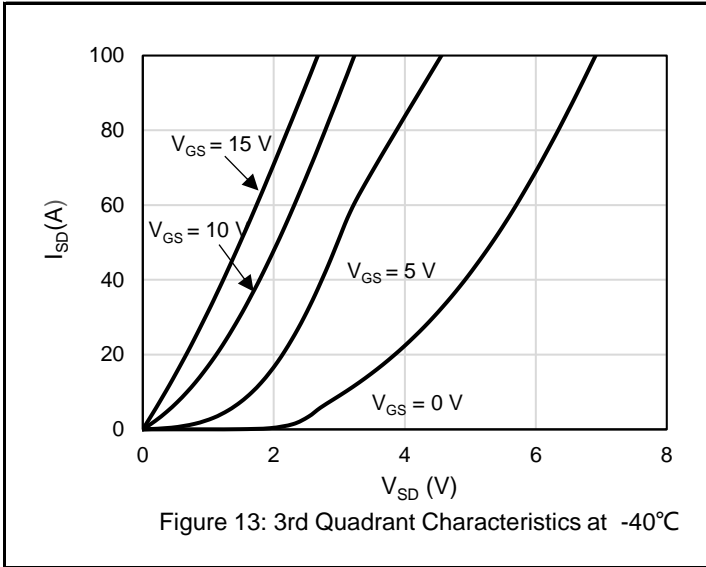
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units	
$T_{D(ON)}$	Turn On Delay Time	$V_{DD} = 800\text{ V}$, $I_D = 33\text{ A}$, $V_{GS} = -4/+15\text{ V}$, $R_{G,EXT} = 2.5\ \Omega$ $L = 99\ \mu\text{H}$ Diode: Body Diode at $V_{GS} = -4\text{ V}$		18		ns	
T_R	Rise Time			42		ns	
$T_{D(OFF)}$	Turn Off Delay Time			33		ns	
T_F	Fall Time			11		ns	
E_{ON}	Turn On Energy				572		μJ
E_{OFF}	Turn Off Energy				56		μJ
$T_{D(ON)}$	Turn On Delay Time	$V_{DD} = 800\text{ V}$, $I_D = 33\text{ A}$, $V_{GS} = -4/+15\text{ V}$, $R_{G,EXT} = 10\ \Omega$ $L = 99\ \mu\text{H}$ Diode: Body Diode at $V_{GS} = -4\text{ V}$		25		ns	
T_R	Rise Time			26		ns	
$T_{D(OFF)}$	Turn Off Delay Time			65		ns	
T_F	Fall Time			18		ns	
E_{ON}	Turn On Energy				1041		μJ
E_{OFF}	Turn Off Energy				225		μJ
$T_{D(ON)}$	Turn On Delay Time	$V_{DD} = 800\text{ V}$, $I_D = 33\text{ A}$, $V_{GS} = -4/+18\text{ V}$, $R_{G,EXT} = 2.5\ \Omega$ $L = 99\ \mu\text{H}$ Diode: Body Diode at $V_{GS} = -4\text{ V}$		7		ns	
T_R	Rise Time			22		ns	
$T_{D(OFF)}$	Turn Off Delay Time			35		ns	
T_F	Fall Time			9		ns	
E_{ON}	Turn On Energy				525		μJ
E_{OFF}	Turn Off Energy				67		μJ
$T_{D(ON)}$	Turn On Delay Time	$V_{DD} = 800\text{ V}$, $I_D = 33\text{ A}$, $V_{GS} = -4/+18\text{ V}$, $R_{G,EXT} = 10\ \Omega$ $L = 99\ \mu\text{H}$ Diode: Body Diode at $V_{GS} = -4\text{ V}$		14		ns	
T_R	Rise Time			37		ns	
$T_{D(OFF)}$	Turn Off Delay Time			67		ns	
T_F	Fall Time			21		ns	
E_{ON}	Turn On Energy				725		μJ
E_{OFF}	Turn Off Energy				237		μJ

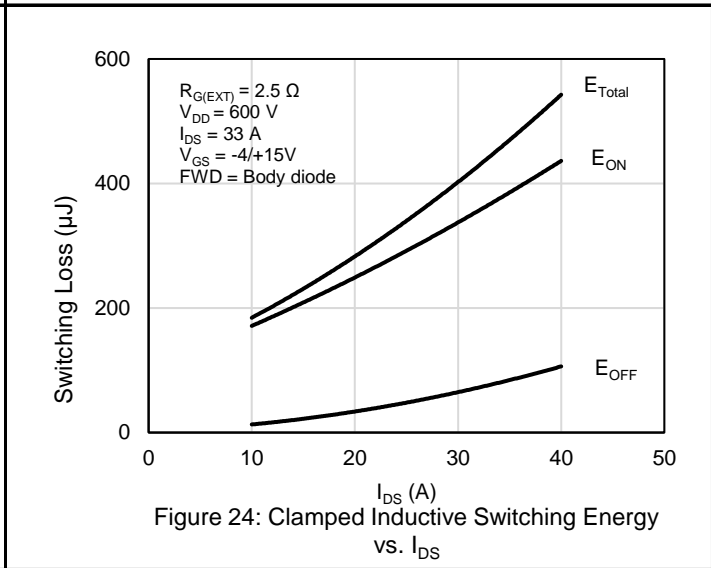
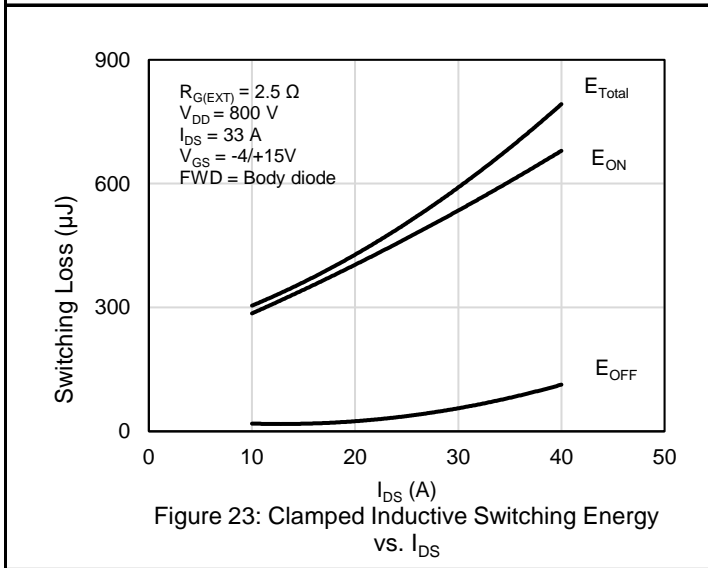
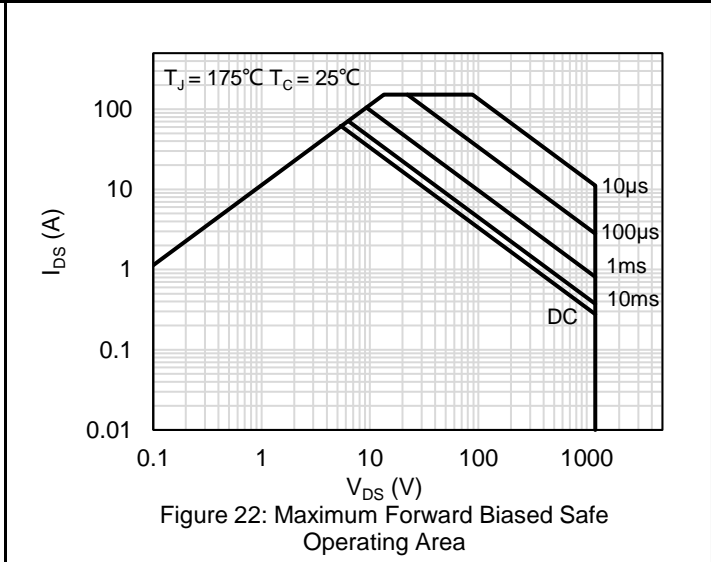
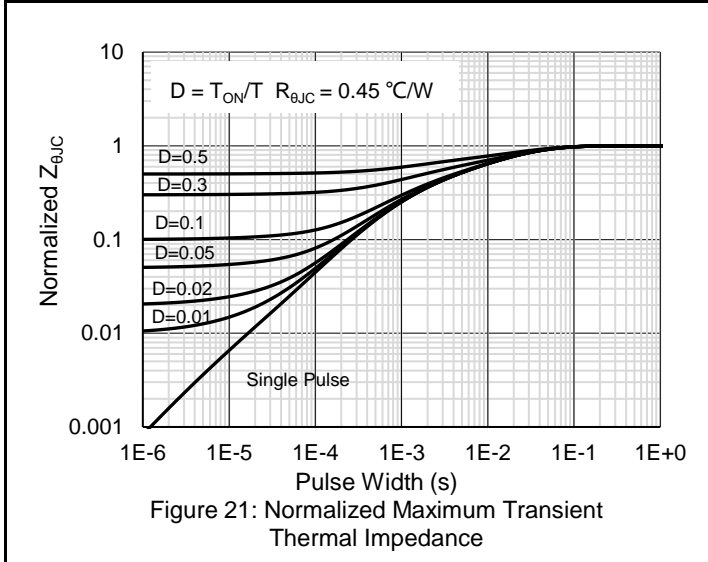
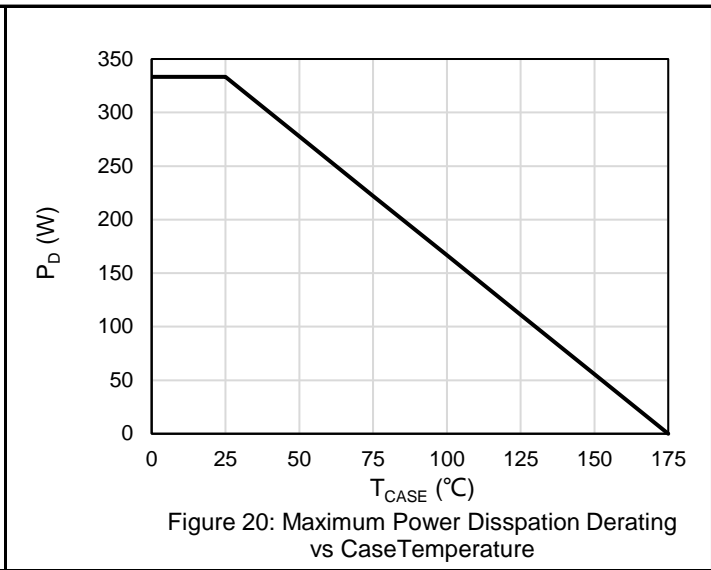
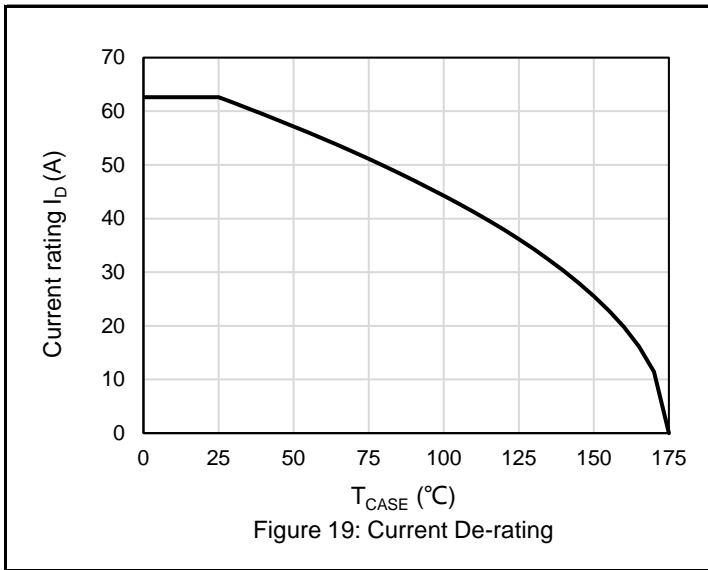
Drain-Source Diode Characteristics ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)					
I_S	Maximum Continuous Drain-Source Diode Forward Current			62	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current			155	A
V_{SD}	Diode Forward Voltage	$V_{GS} = -4\text{ V}, I_{SD} = 20\text{ A}$		5.5	V
		$V_{GS} = -4\text{ V}, I_{SD} = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$		5	V
I_{RM}	Peak Reverse Recovery Current	$V_{GS} = -4\text{ V}, I_{SD} = 33\text{ A}, V_R = 800\text{ V}, di/dt = 4200\text{ A}/\mu\text{s}$		26	A
T_{RR}	Reverse Recovery Time			17	ns
Q_{RR}	Reverse Recovery Charge			133	nC

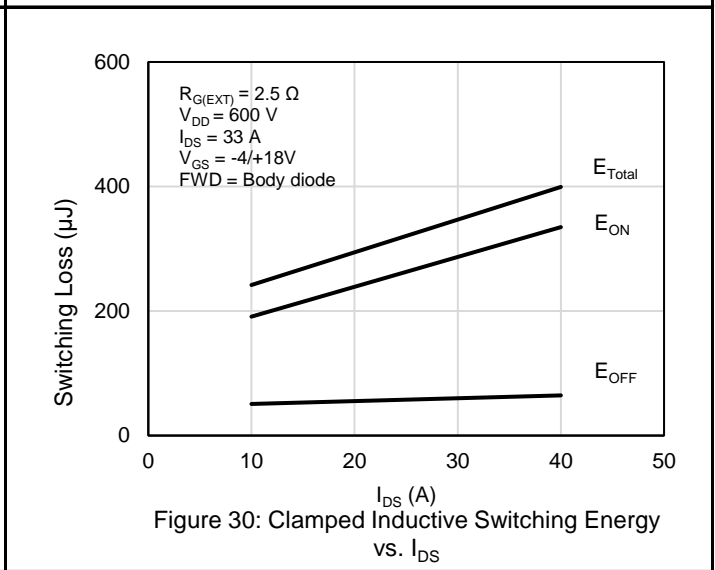
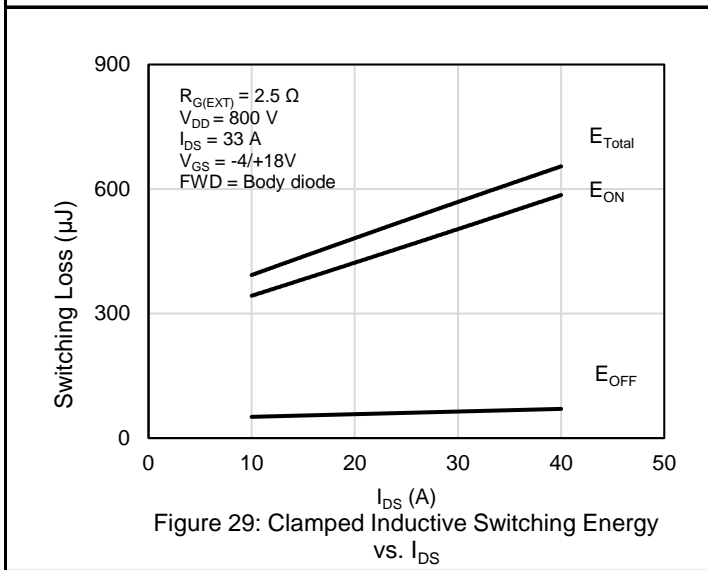
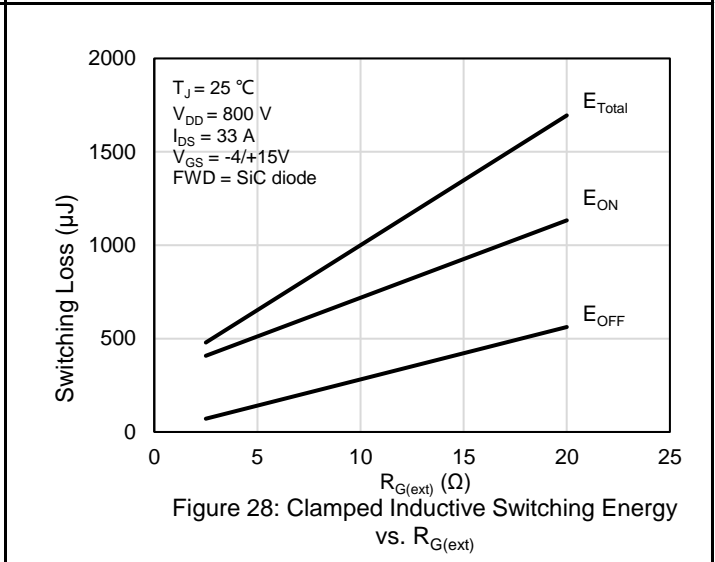
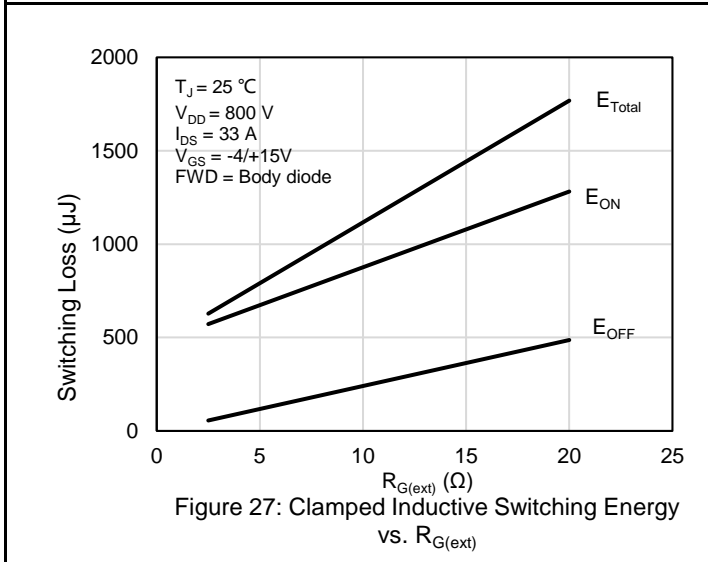
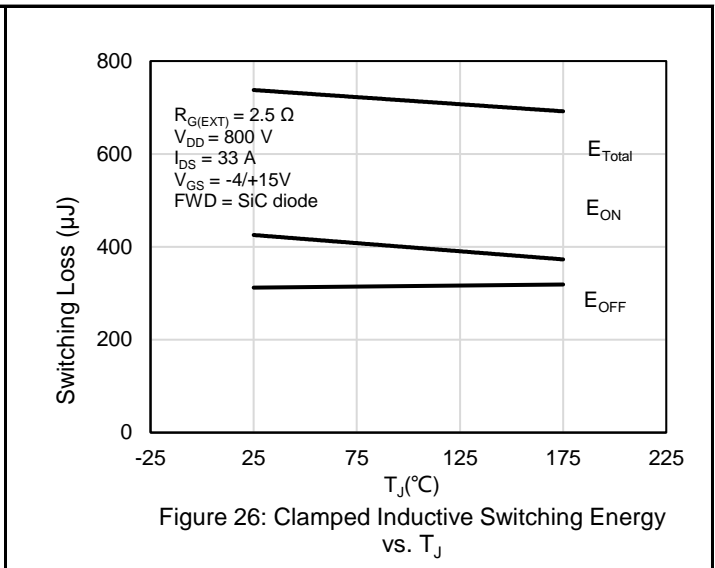
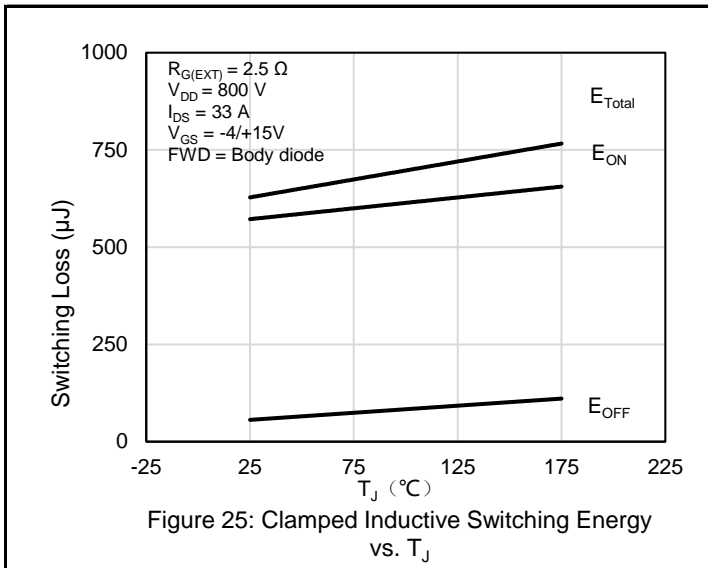
Electrical Characteristics Diagrams

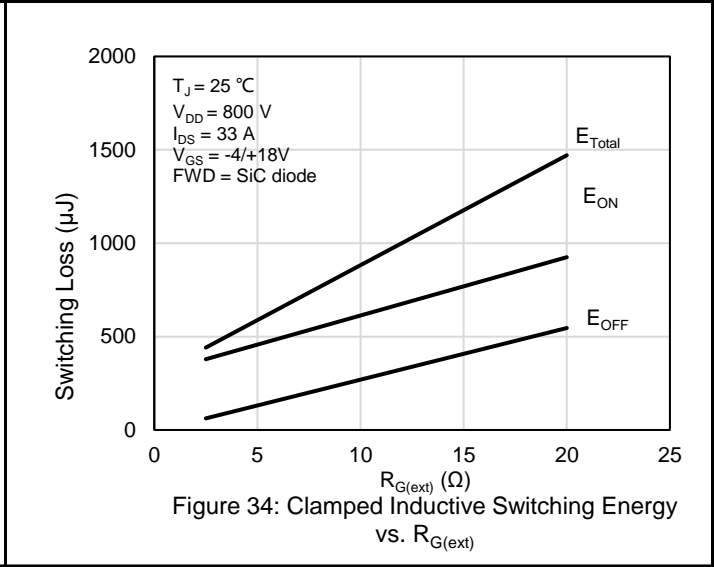
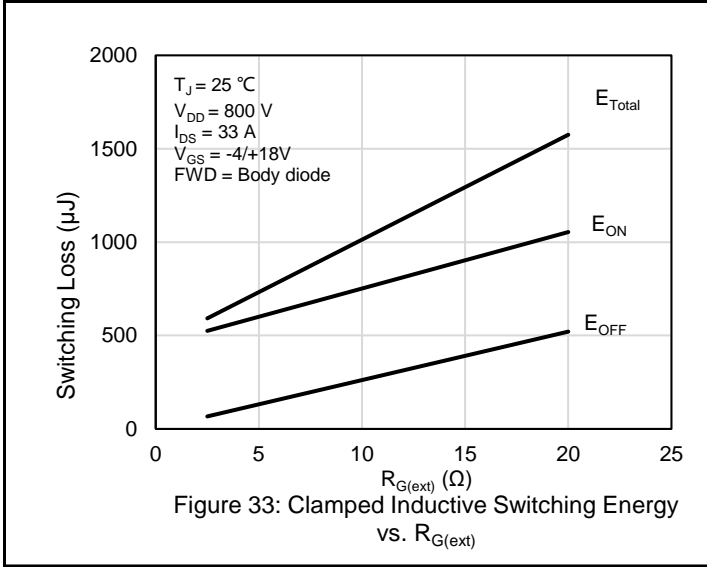
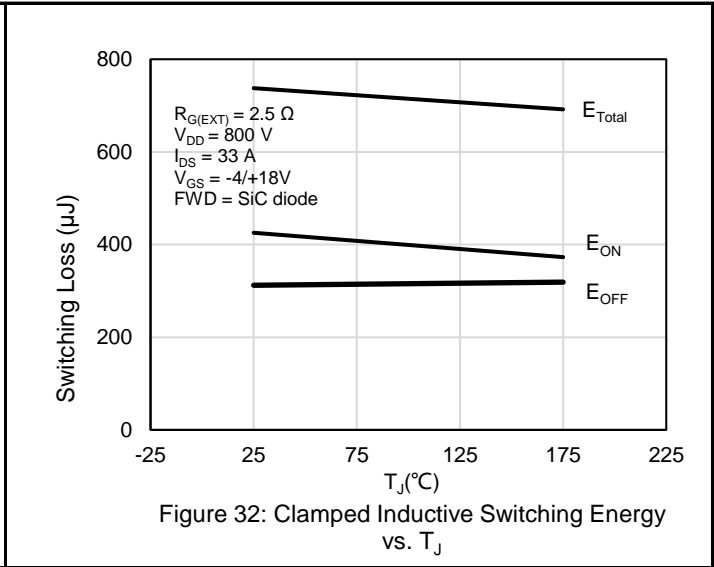
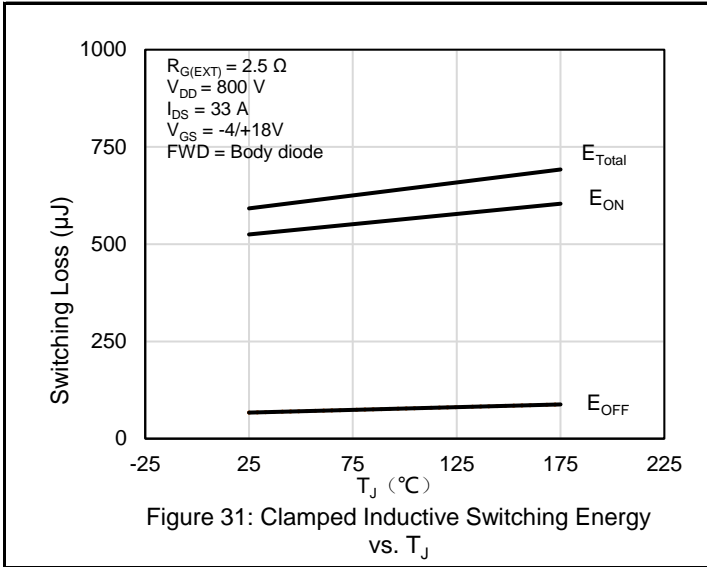






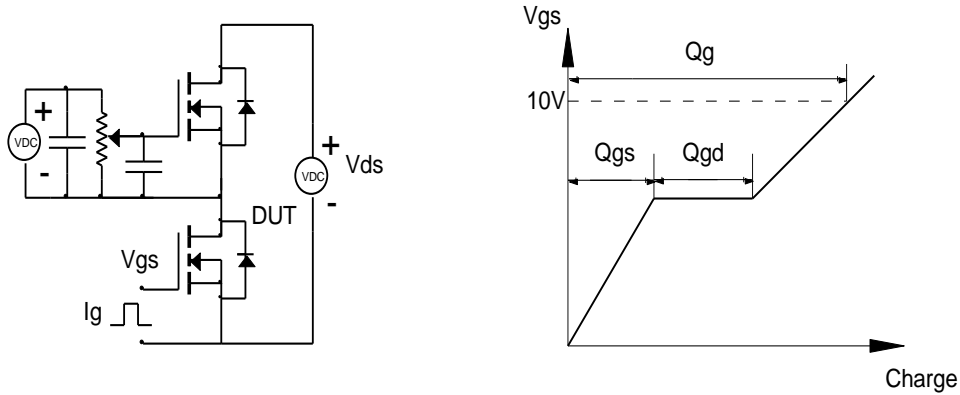




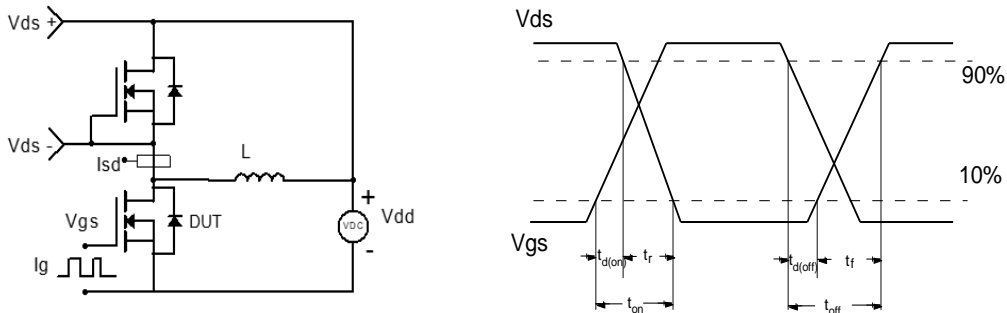


Test Circuit and Waveform

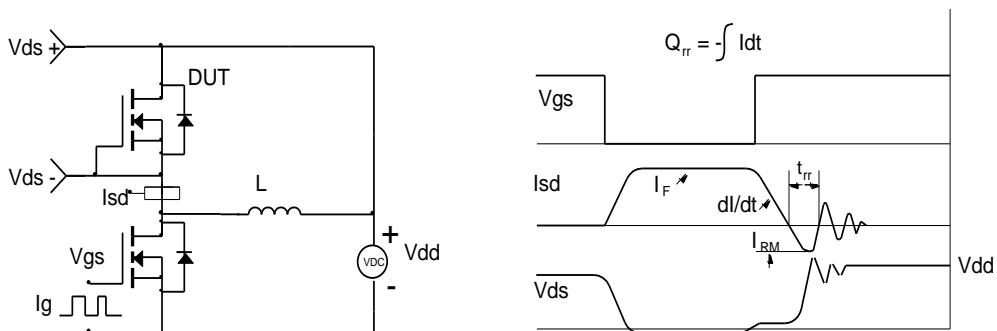
Gate Charge Test Circuit & Waveform



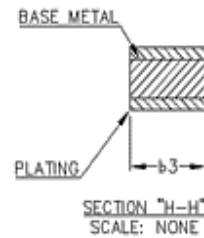
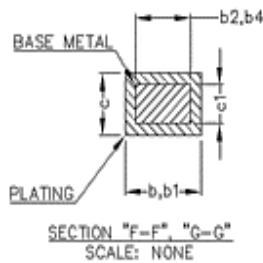
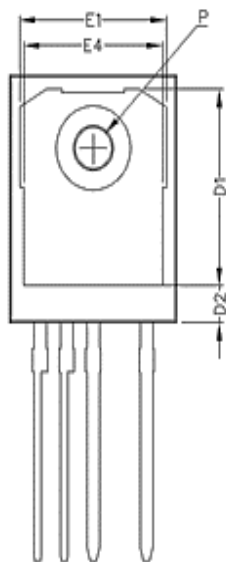
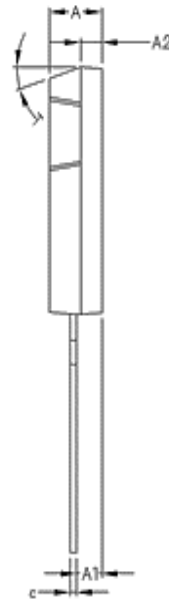
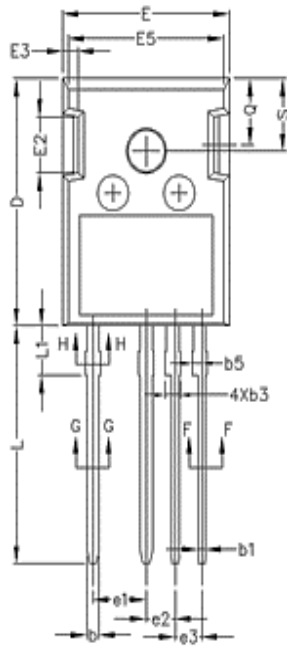
Clamped Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

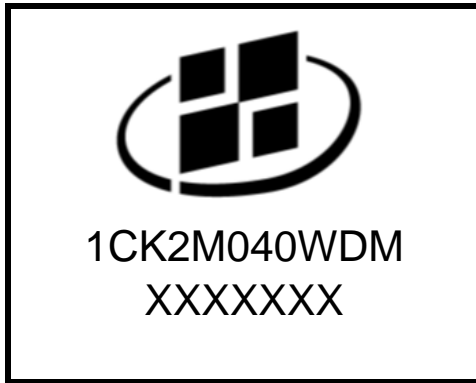


Package Outlines



SYMBOL	MIN	MAX
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b	1.10	1.30
b1	0.65	0.79
b2	1.10	1.25
b3	1.34	1.44
b4	0.65	0.74
b5	0.74	1.14
c	0.55	0.68
c1	0.55	0.65
D	20.80	21.10
D1	16.25	17.65
D2	2.95	3.35
E	15.75	16.13
E1	13.10	14.15
E2	4.32	5.10
E3	1.00	1.90
E4	12.38	13.43
E5	14.65	15.05
e1	5.08 BSC	
e2	2.79 BSC	
e3	2.54 BSC	
L	19.72	20.32
L1	3.97	4.37
øP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
T	17.5° REF.	

Marking Information



Note:

1CK2M040WDM = Product Name Code

XXXXXXX = Date Code

Contact ALKAIDSEMI sales for detail information

Revision History		
Revision	Release Date	Remark
Rev.1.0	2024	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements, the information described or contained herein may be changed without prior notice.